



New Generation of InGaN Layers, Quantum Wells and Wires Grown on Vicinal GaN Substrates for Optoelectronics and Photovoltaics **WiseGaN**

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Visegrad Group (V4) + Japan
- *Innovation and Industry* -

Joint Science Diplomacy Seminar

9th March 2022

GaNification

Gallium nitride based devices: second (after silicon-based) semiconductor market

Institute of High Pressure Physics

Director Iza Grzegory



GaN substrate growth, M. Bockowski +15+ Ammono (20)



MBE growth, C. Skierbiszewski+15

MOVPE growth, Electronic devices,
Microstructure, M. Leszczynski+12

Laser processing, P. Perlin+12

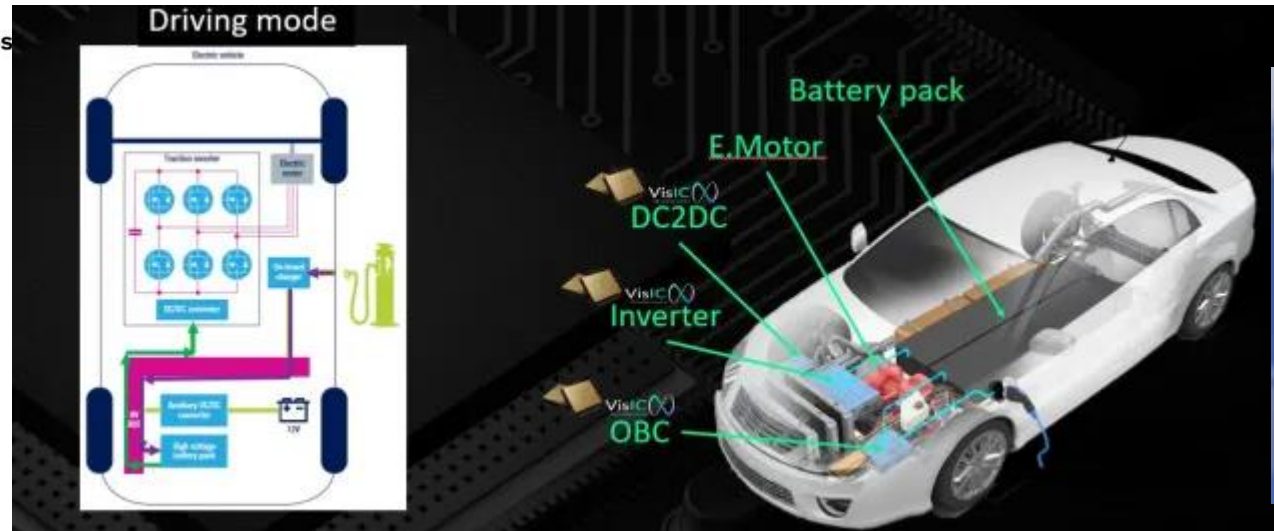
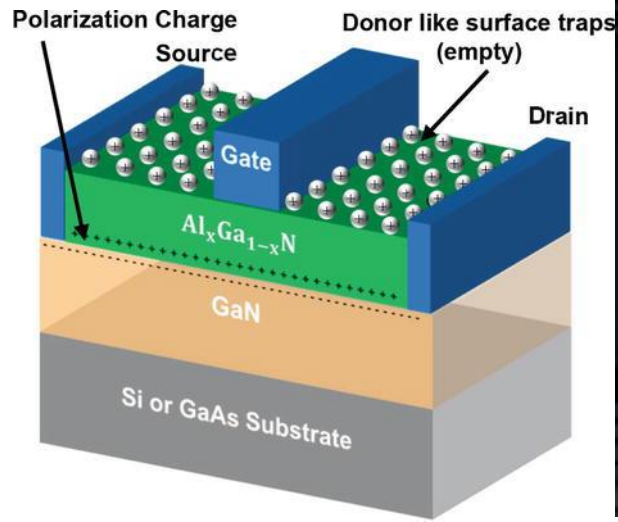
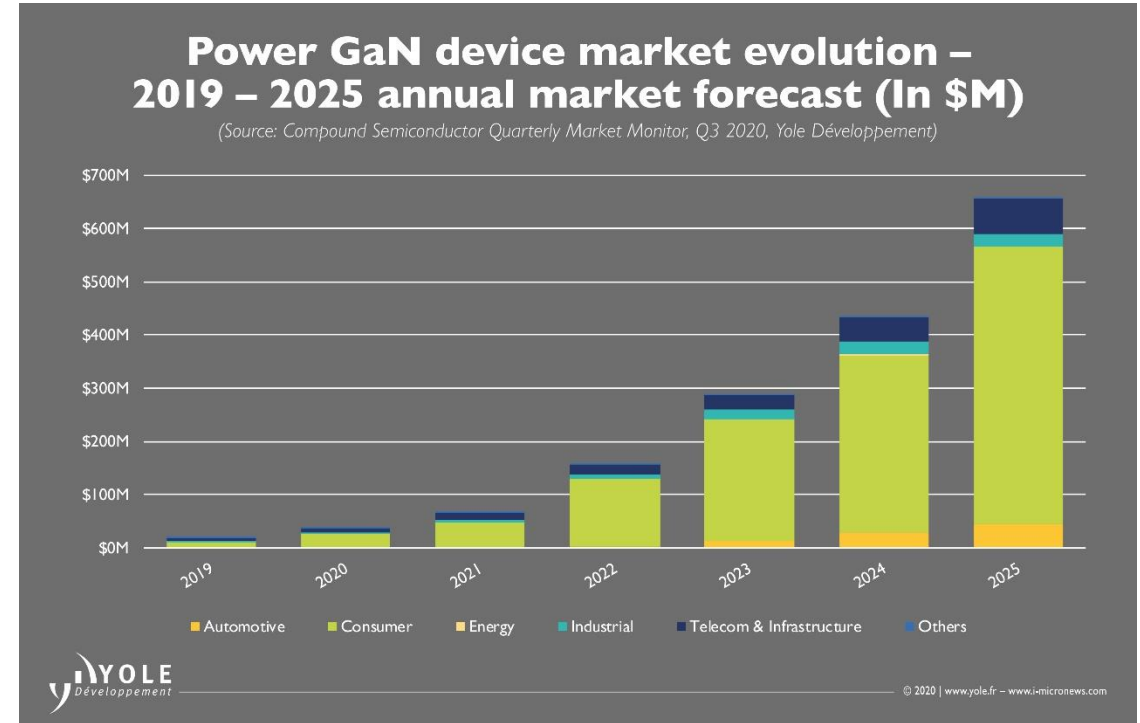
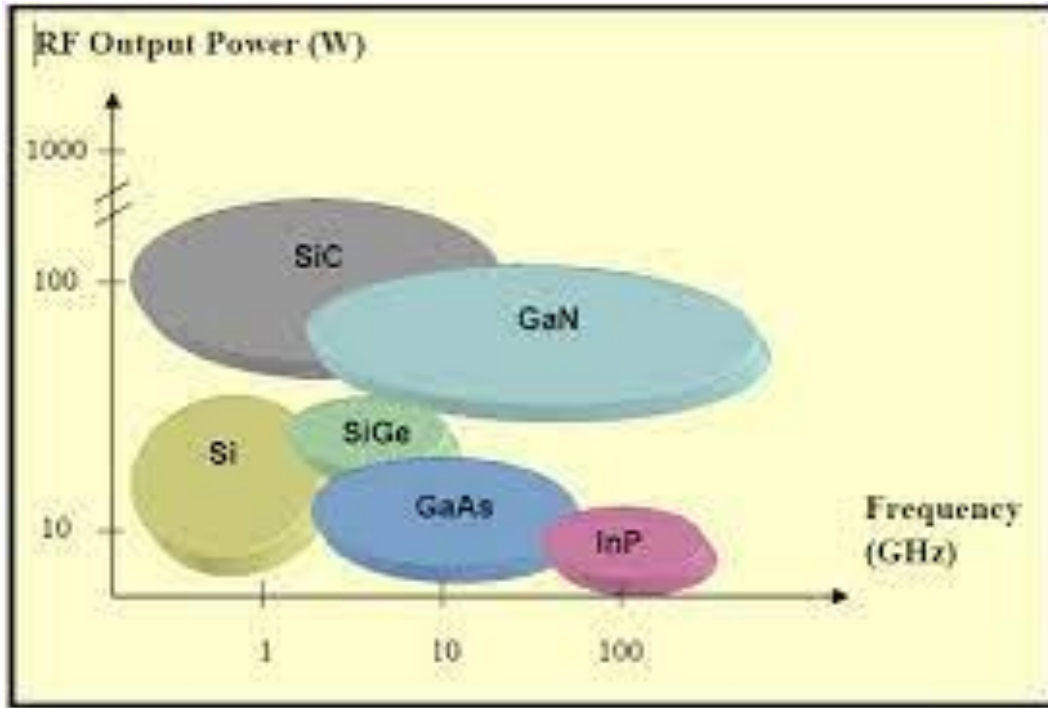
Physics of semiconductors, T. Suski+8



Manufacturing, A. Kasprowiak,
K. Wegrzyn, M. Leszczynski,
P. Perlin +15

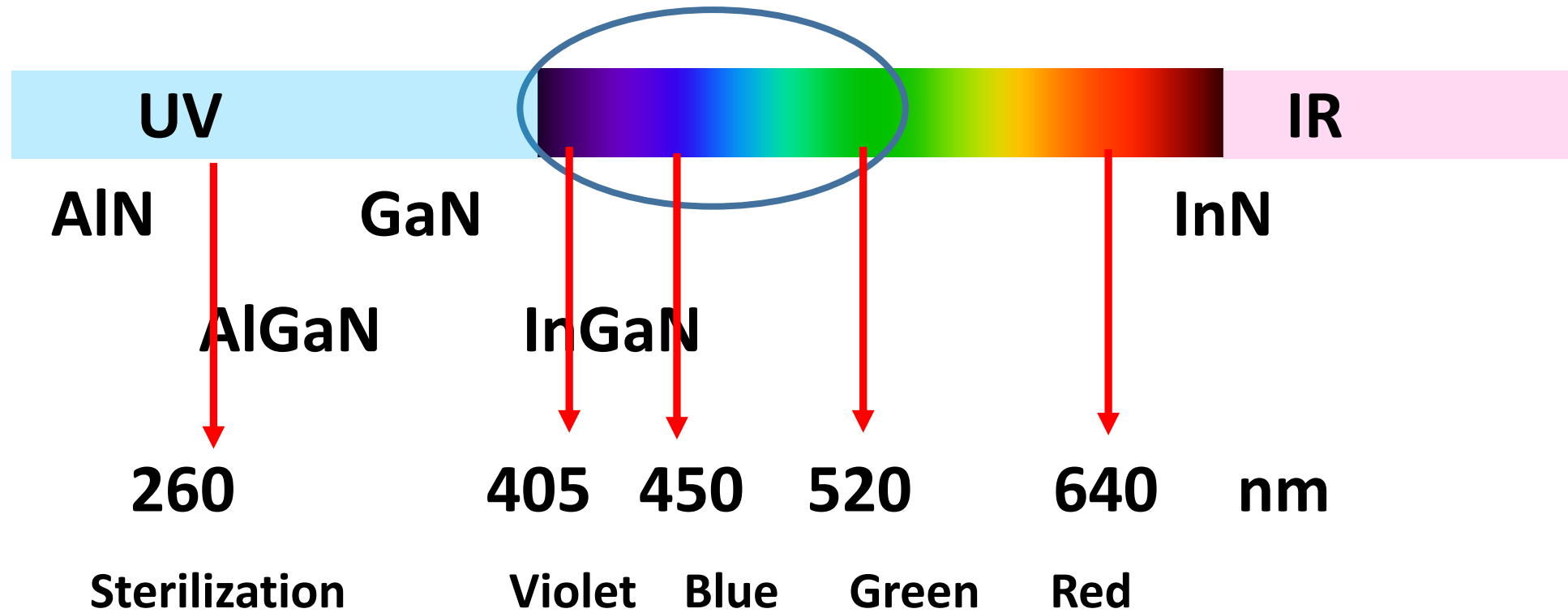
In total, about 100 engineers and scientists

GaN-based Transistors

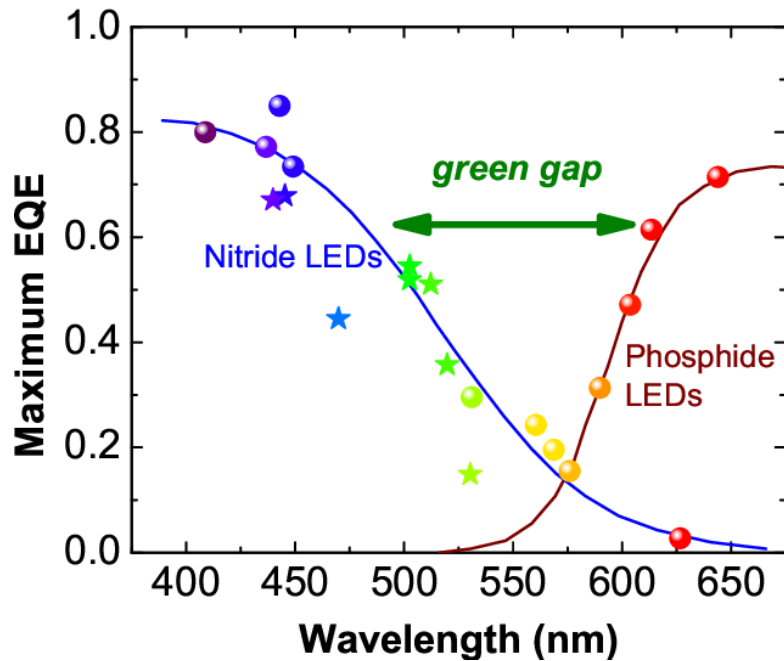
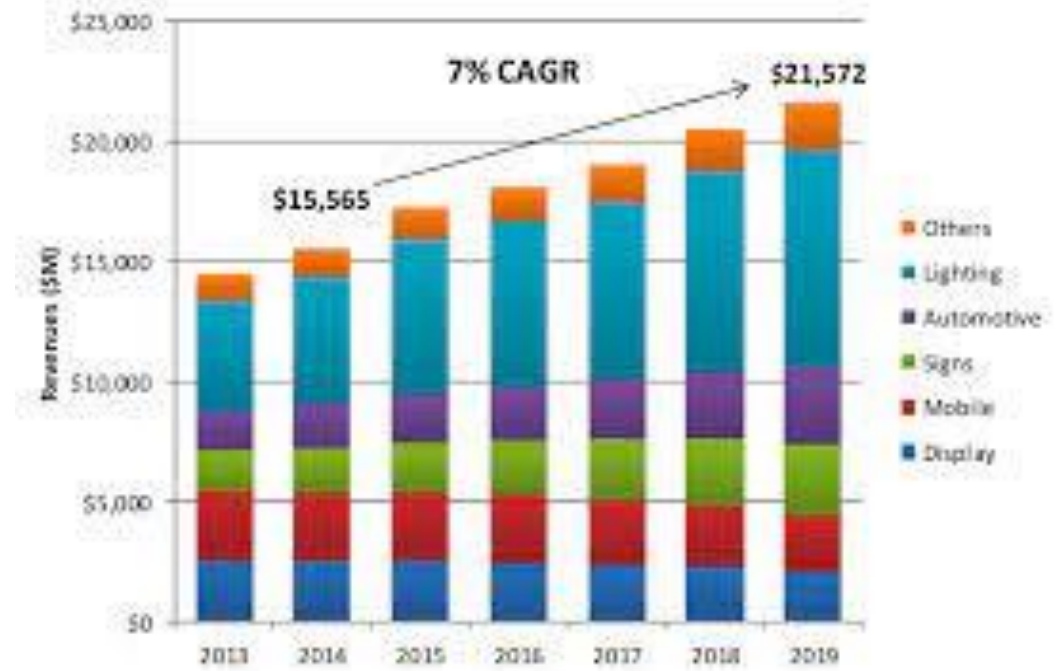
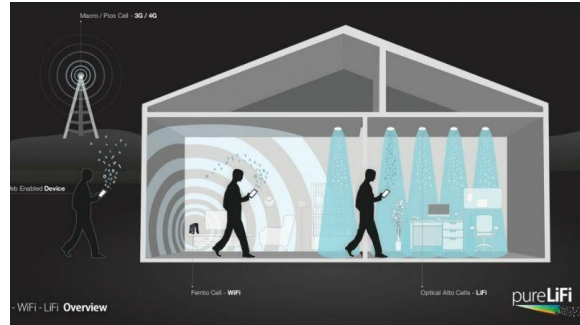


Nitrides:

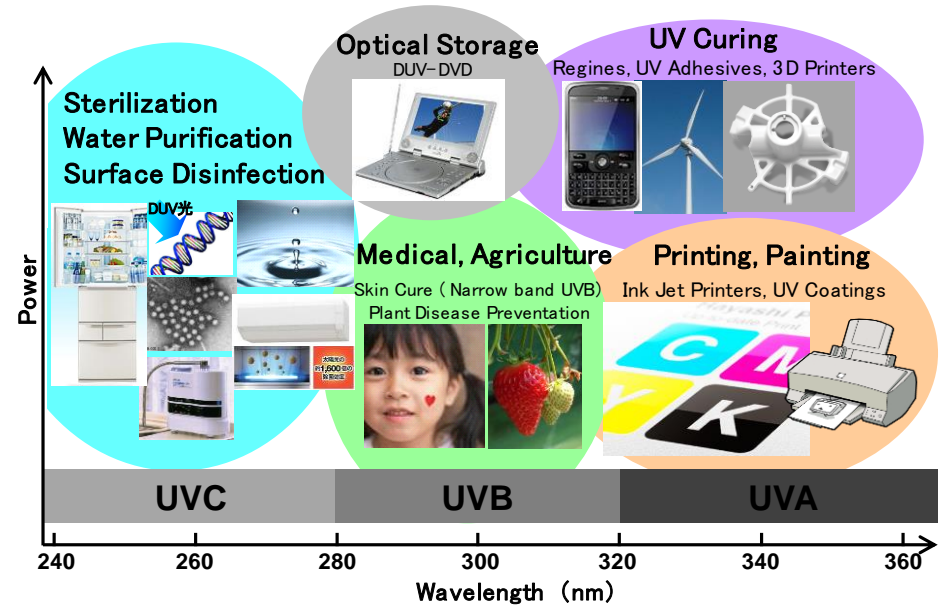
Energy gap from IR to UVC, strong bonds



LEDs



★
260



Laser Diodes (LDs)



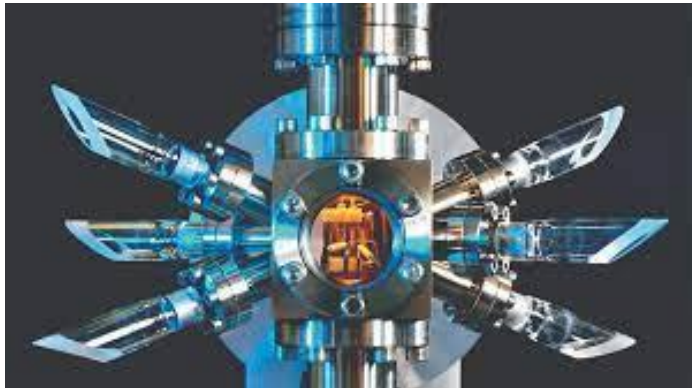
Blue ray



Headlight lamps



Copper welding



Atomic clocks



Laser projectors



Underwater communication

WiseGaN



Mike Leszczynski
Unipress

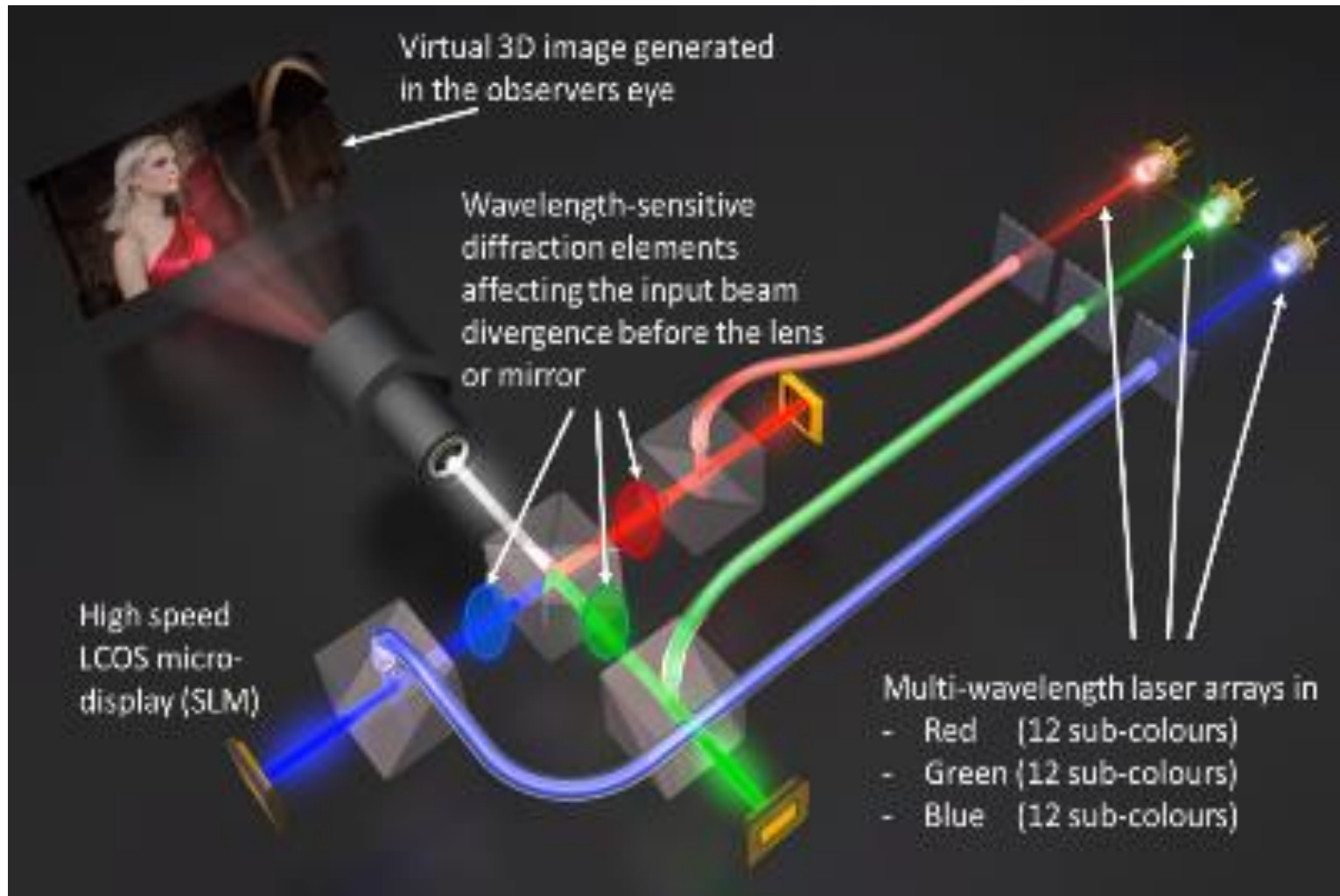


Hiroshi Amano Nagoya University
Nobel Prize 2014



Vaclav Holy Charles University
Famous X-ray Specialist

3-D Projectors without goggles- Holy Grail of optoelectronics



Nitrides:

Blue 450-460 nm, step 1 nm

Green 520-530 nm, step 1 nm

Arsenides/phosphides

Red 630-640 nm, step 1 nm

Project WiseGaN was an important step towards 3D projectors, but still many problems must be solved.

In 4-5 years, such 3D laser projectors should be on the markets. There is a chance that they will be based on WiseGaN technology.

